



New Product

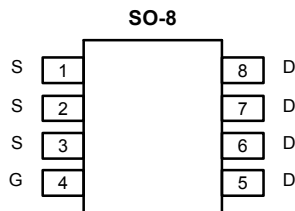
Si9410BDY
Vishay Siliconix

N-Channel 30-V (D-S) MOSFET

PRODUCT SUMMARY		
V_{DS} (V)	$r_{DS(on)}$ (Ω)	I_D (A)
30	0.024 @ $V_{GS} = 10$ V	8.1
	0.033 @ $V_{GS} = 4.5$ V	6.9

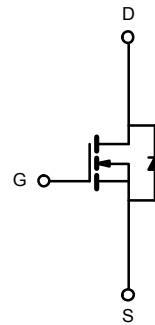
FEATURES

- TrenchFET® Power MOSFETS



Top View

Ordering Information: Si9410BDY
Si9410BDY-T1 (with Tape and Reel)



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)					
Parameter		Symbol	10 secs	Steady State	Unit
Drain-Source Voltage		V_{DS}	30		V
Gate-Source Voltage		V_{GS}	± 20		
Continuous Drain Current ($T_J = 150^\circ\text{C}$) ^a	$T_A = 25^\circ\text{C}$	I_D	8.1	6.2	A
	$T_A = 70^\circ\text{C}$		6.5	5.0	
Pulsed Drain Current (10 μs Pulse Width)		I_{DM}	30		
Continuous Source Current (Diode Conduction) ^a		I_S	2.1	1.2	W
Maximum Power Dissipation ^a	$T_A = 25^\circ\text{C}$	P_D	2.5	1.5	
	$T_A = 70^\circ\text{C}$		1.6	0.9	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	-55 to 150		$^\circ\text{C}$

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^a	$t \leq 10$ sec	R_{thJA}	40	50	$^\circ\text{C/W}$
	Steady State		70	85	
Maximum Junction-to-Foot		R_{thJF}	20	24	

Notes

a. Surface Mounted on 1" x 1" FR4 Board.

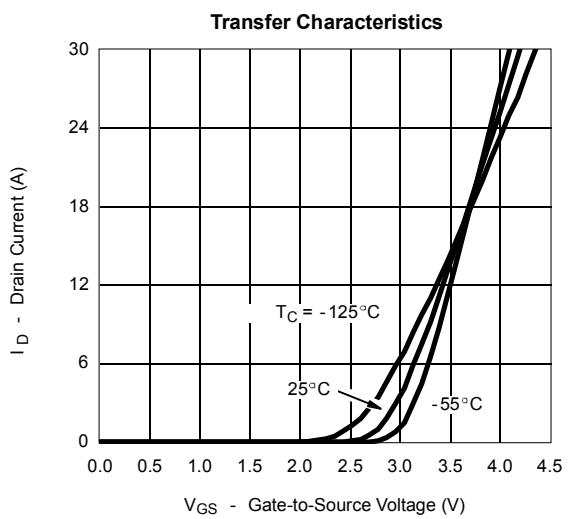
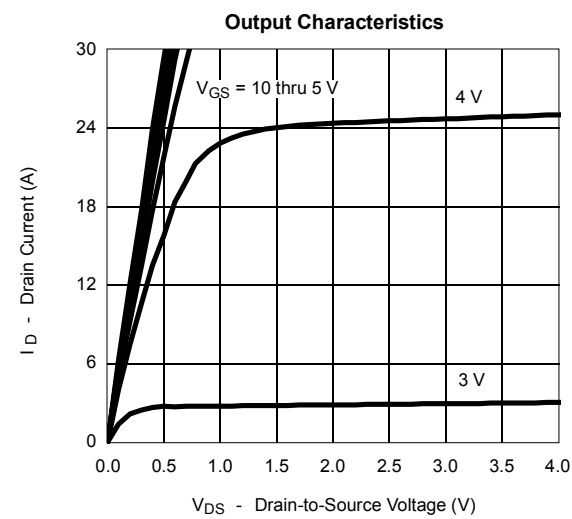


SPECIFICATIONS (T _J = 25°C UNLESS OTHERWISE NOTED)						
Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Static						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	1.0		3.0	V
Gate-Body Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ±20 V			±100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 24 V, V _{GS} = 0 V			1	μA
		V _{DS} = 24 V, V _{GS} = 0 V, T _J = 55°C			5	
On-State Drain Current ^a	I _{D(on)}	V _{DS} ≥ 5 V, V _{GS} = 10 V	30			A
Drain-Source On-State Resistance ^a	r _{DS(on)}	V _{GS} = 10 V, I _D = 8.1 A		0.019	0.024	Ω
		V _{GS} = 4.5 V, I _D = 6.9 A		0.026	0.033	
Forward Transconductance ^a	g _{fs}	V _{DS} = 15 V, I _D = 8.1 A		20		S
Diode Forward Voltage ^a	V _{SD}	I _S = 2.1 A, V _{GS} = 0 V		0.8	1.2	V
Dynamic^b						
Total Gate Charge	Q _g	V _{DS} = 15 V, V _{GS} = 10 V, I _D = 8.1 A		15	23	nC
Gate-Source Charge	Q _{gs}			3.2		
Gate-Drain Charge	Q _{gd}			2.5		
Turn-On Delay Time	t _{d(on)}	V _{DD} = 15 V, R _L = 15 Ω I _D ≅ 1 A, V _{GEN} = 10 V, R _G = 6 Ω		10	15	ns
Rise Time	t _r			15	25	
Turn-Off Delay Time	t _{d(off)}			30	45	
Fall Time	t _f			11	20	
Source-Drain Reverse Recovery Time	t _{rr}	I _F = 2.1 A, di/dt = 100 A/μs		25	50	

Notes

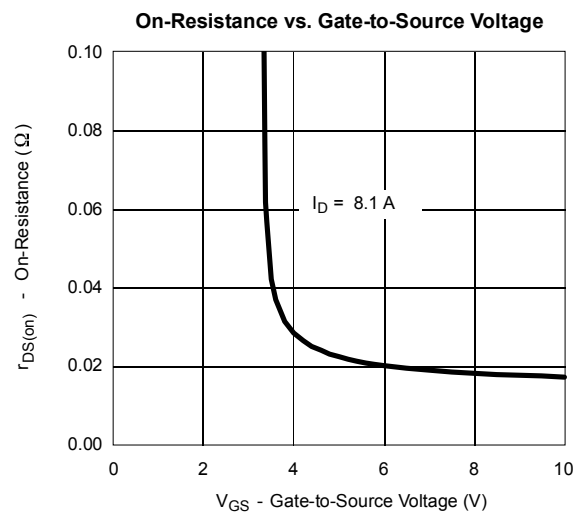
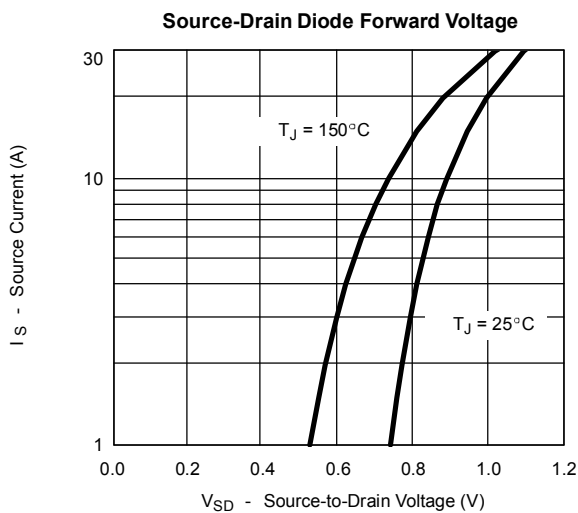
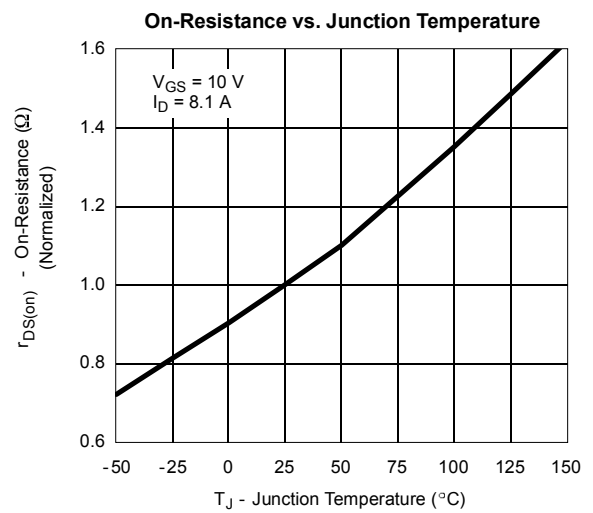
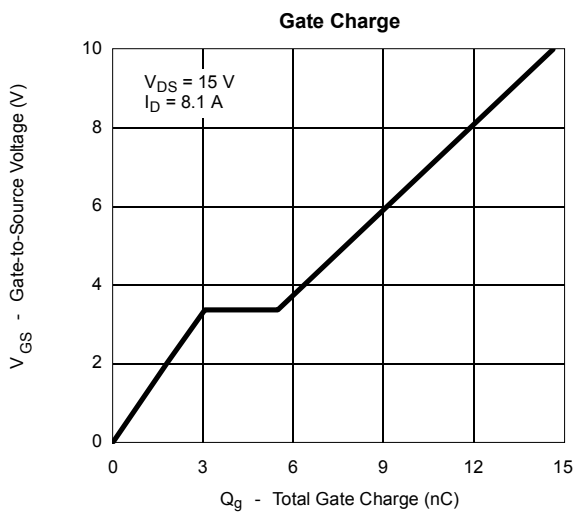
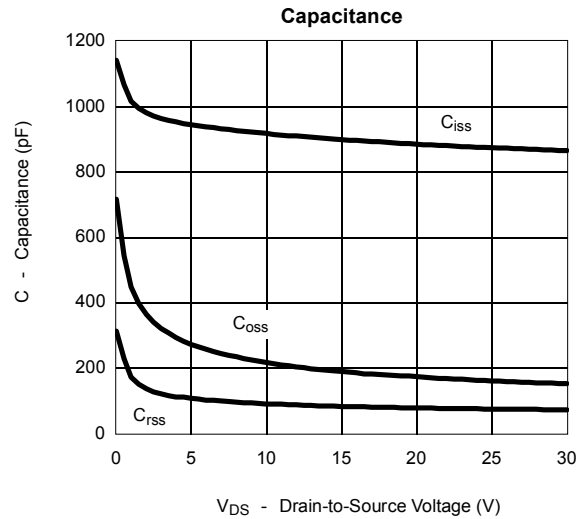
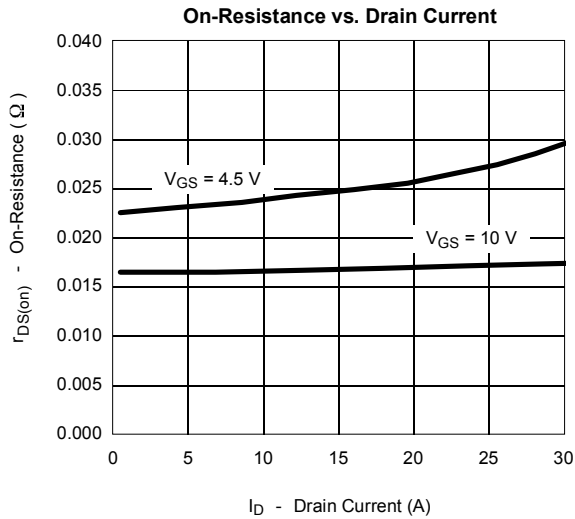
- a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2%.
- b. Guaranteed by design, not subject to production testing.

TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)



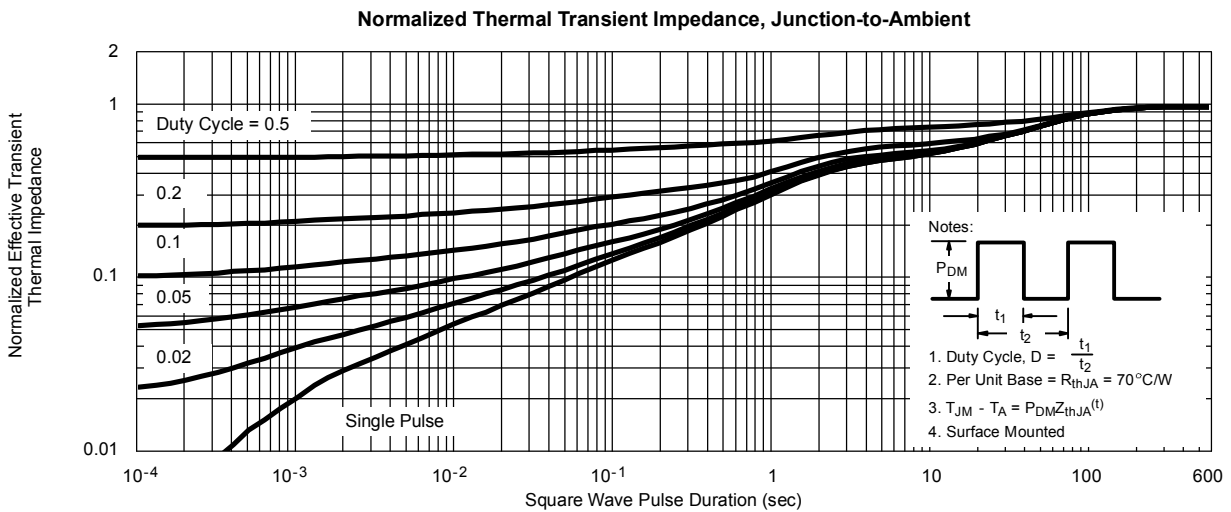
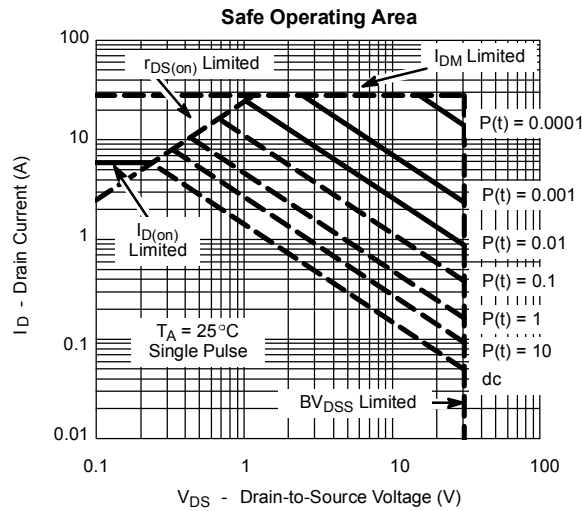
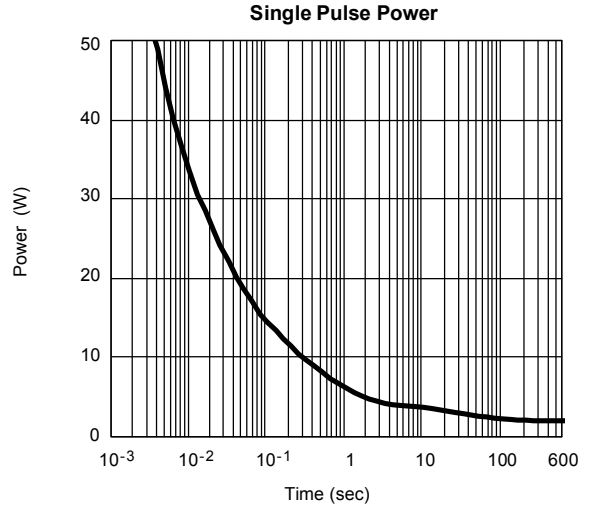
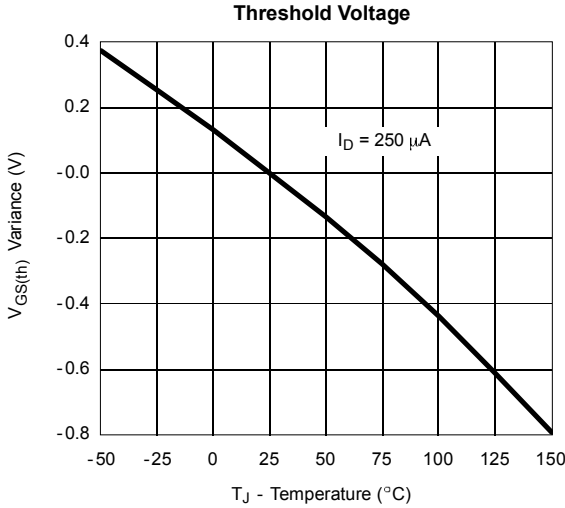


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